



DMN10H170SFG

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	l _D max T _A = +25°C		
4001/	122mΩ @ V _{GS} = 10V	2.9A		
100V	133mΩ @ V _{GS} = 4.5V	2.7A		

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

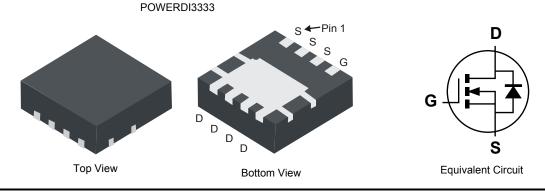
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

Features

- 100% Unclamped Inductive Switch (UIS) test in production
- Low RDS(ON) ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: POWERDI3333
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.034 grams (approximate)



Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN10H170SFG-7	Standard	POWERDI3333	2000/Tape & Reel
DMN10H170SFG-13	Standard	POWERDI3333	3000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

Notes:

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



G17 = Product marking code YYWW = Date code marking YY = Last digit of year (ex: 10 for 2010) WW = Week code (01 - 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ $T_C = +25^{\circ}C$	ID	2.9 2.4 8.5	А
	t<10s	T _A = +25°C T _A = +70°C	ID	3.7 3.0	А
Maximum Continuous Body Diode Forward Current (Note 6)			Is	3.0	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	16	А
Avalanche Current (Note 7)			lar	5.3	А
Avalanche Energy (Note 7)			Ear	20	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Dower Dissinction (Note 5)	T _A = +25°C	D	0.94	W
Total Power Dissipation (Note 5)	T _A = +70°C	PD	0.6	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Р	137	°C/W
mermai Resistance, Junction to Ambient (Note 5)	t<10s	R _{θJA}	82	°C/W
Total Dower Discipation (Note 6)	T _A = +25°C	D	2.0	W
Total Power Dissipation (Note 6)	T _A = +70°C	PD	1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Р	60	°C/W
member (Note 6)	t<10s	R _{θJA}	36	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	7.0	°C/W
Operating and Storage Temperature Range		T _{J.} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Мах	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	V _{GS} = 0V, I _D = 250µA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μA	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	000						
Gate Threshold Voltage	V _{GS(th)}	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Statia Dusia Course On Desistence			99	122		V _{GS} = 10V, I _D = 3.3A	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	104	133	mΩ	V _{GS} = 4.5V, I _D = 3.0A	
Forward Transfer Admittance	Y _{fs}		4.4		S	V _{DS} = 10V, I _D = 3.3A	
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 3.3A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	870.7	_	pF		
Output Capacitance	Coss	_	40.8		pF	−V _{DS} = 25V, V _{GS} = 0V, −f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		24.6		pF		
Gate resistance	Rq	_	1.1		Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz	
Total Gate Charge (V _{GS} = 4.5V)	Qg		7.0		nC		
Total Gate Charge (V _{GS} = 10V)	Qq	_	14.9		nC		
Gate-Source Charge	Q _{gs}		3.3		nC	$-V_{DS} = 50V, I_{D} = 3.3A$	
Gate-Drain Charge	Q _{qd}	_	3.0		nC	7	
Turn-On Delay Time	t _{D(on)}	_	4.4		ns		
Turn-On Rise Time	tr		2.3	_	ns	V _{DD} = 50V, V _{GEN} = 10V,	
Turn-Off Delay Time	t _{D(off)}	_	13.9	_	ns	$R_{GEN} = 6.0\Omega, I_D = 3.3A$	
Turn-Off Fall Time	tr		3.4		ns		
Reverse Recovery Time	t _{rr}		22.4		ns		
Reverse Recovery Charge	Q _{rr}	—	19.7	—	nC	– I _S = 3.3A, dI/dt = 100A/µs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

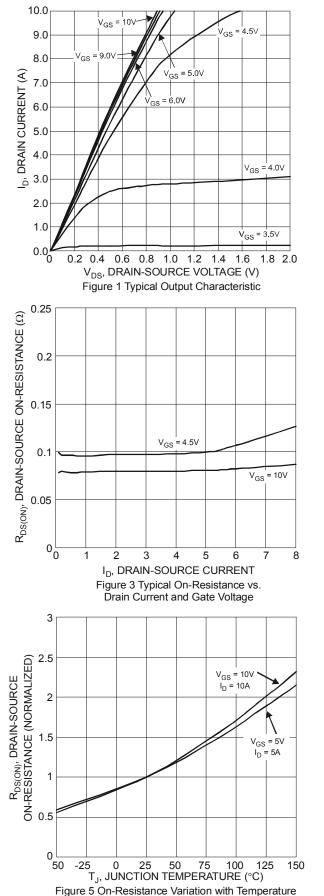
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. 7. UIS in production with L = 1.43mH, T_J = $+25^{\circ}$ C.

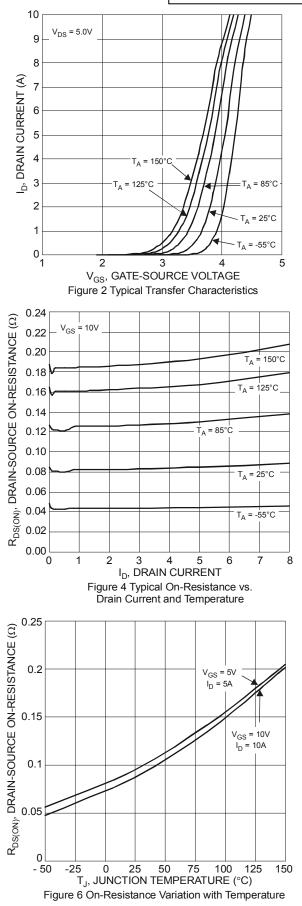
8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.





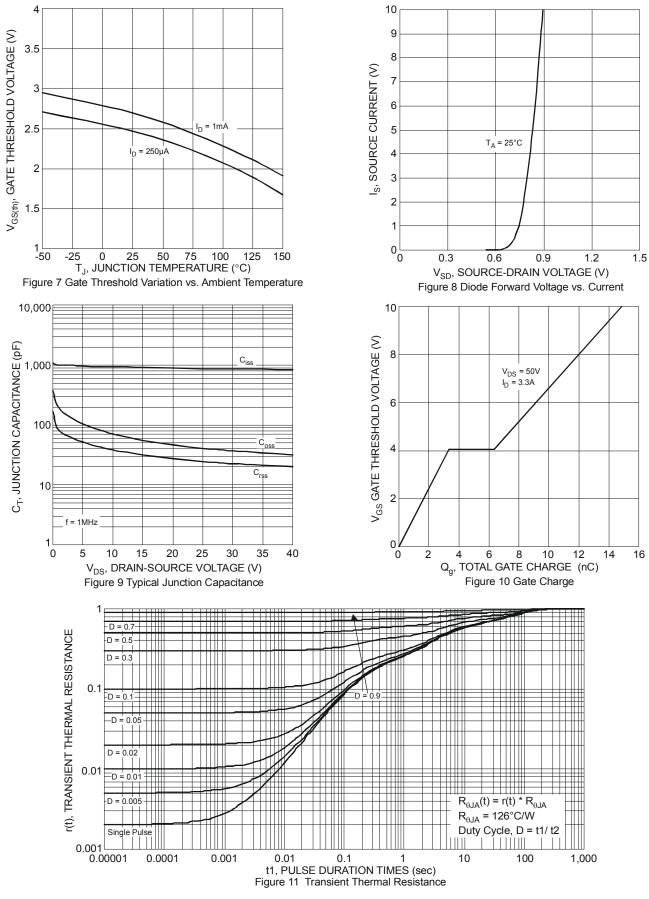




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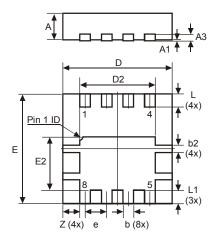


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Package Outline Dimensions

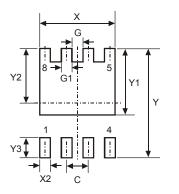
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



POWERDI3333-8						
Dim	Min	Max	Тур			
D	3.25	3.35	3.30			
Е	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
E2	1.56	1.66	1.61			
Α	0.75	0.85	0.80			
A1	0	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	-	-	0.20			
L	0.35	0.45	0.40			
L1	-	-	0.39			
е	_	_	0.65			
Ζ	_	_	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	0.650			
G	0.230			
G1	0.420			
Y	3.700			
Y1	2.250			
Y2	1.850			
Y3	0.700			
Х	2.370			
X2	0.420			



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